

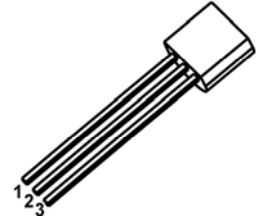
TO-92 Plastic-Encapsulate Transistors

BC556/BC557/BC558 TRANSISTOR (PNP)

FEATURES

- High Voltage
- Complement to BC546,BC547,BC548

TO - 92



1. COLLECTOR
2. BASE
3. EMITTER

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	BC556	-80
		BC557	-50
		BC558	-30
V_{CEO}	Collector-Emitter Voltage	BC556	-65
		BC557	-45
		BC558	-30
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.1	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter		Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BC556	V _{(BR)CBO}	I _C = -0.1mA, I _E =0	-80			V
	BC557			-50			
	BC558			-30			
Collector-emitter breakdown voltage	BC556	V _{(BR)CEO}	I _C =-2mA, I _B =0	-65			V
	BC557			-45			
	BC558			-30			
Emitter-base breakdown voltage		V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	BC556	I _{CBO}	V _{CB} =-70V, I _E =0			-0.1	μA
	BC557		V _{CB} =-45V, I _E =0			-0.1	μA
	BC558		V _{CB} =-25V, I _E =0			-0.1	μA
Collector cut-off current	BC556	I _{CEO}	V _{CE} =-60V, I _B =0			-0.1	μA
	BC557		V _{CE} =-40V, I _B =0			-0.1	μA
	BC558		V _{CE} =-25V, I _B =0			-0.1	μA
Emitter cut-off current		I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain		h _{FE}	V _{CE} =-5V, I _C =-2mA	120		800	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA			-0.3	V
			I _C =-100mA, I _B =-5mA			-0.65	V
Base-emitter saturation voltage		V _{BE(sat)}	I _C =-10mA, I _B =-0.5mA			-0.8	V
			I _C =-100mA, I _B =-5mA			-1	V
Base-emitter voltage		V _{BE}	V _{CE} =-5V, I _C =-2mA	-0.55		-0.7	V
			V _{CE} =-5V, I _C =-10mA			-0.82	V
Collector output capacitance		C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			6	pF
Transition frequency	BC556	f _T	V _{CE} =-5V, I _C =-10mA, f=100MHz		150		MHz
	BC557				150		MHz
	BC558				150		MHz

CLASSIFICATION of h_{FE}

RANK	A	B	C
RANGE	120-220	180-460	420-800

TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

TO-92 PACKAGE TAPEING DIMENSION



Dimiensions are in millimeter								
A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250